

upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

49. (new) A method for reducing the contamination on a semiconductor wafer from a wet etching bath comprising:

processing said semiconductor wafer in said wet etching bath containing an etching fluid;

subsequently suddenly removing an upper portion of said etching fluid from said wet etching bath to remove contaminants from the surface of said wet etching bath while retaining said semiconductor wafer in said wet etching bath, in a manner such that the velocity of said upper portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value; and

subsequently removing said semiconductor wafer from said wet etching bath.

50. (new) A method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, by opening a valve in said bath in a manner such that the velocity of said upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

51. (new) A method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, by hingedly releasing a door located at an upper portion of said bath in a

manner such that the velocity of said upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

52. (new) A method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, by sliding a door located at an upper portion of said bath in a manner such that the velocity of said upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

53. (new) A method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, by rapidly removing a wafer boat containing said semiconductor wafer from said bath in a manner such that the velocity of said upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

54. (new) A method for removing contaminants from a semiconductor processing bath for processing semiconductor wafers, said method comprising removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, by telescopically collapsing sidewalls of a vessel containing said bath in a manner such that the velocity of said upper portion of said semiconductor processing fluid rapidly increases at the point of removal from a first value to a second higher value.

55. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time;

removing a portion of said etching fluid from the upper surface of said wet etching vessel while keeping said semiconductor wafer immersed in said etching fluid, in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value; and

removing said semiconductor wafer from said etching fluid.

56. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

removing a portion of said etching fluid from the upper surface of said wet etching vessel by opening a valve in said wet etching vessel in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value.

57. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

removing a portion of said etching fluid from the upper surface of said wet etching vessel by hingedly releasing a door located at an upper portion of said wet etching vessel in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value.

58. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

removing a portion of said etching fluid from the upper surface of said wet etching vessel by sliding a door located at an upper portion of said wet etching vessel in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value.

59. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

removing a portion of said etching fluid from the upper surface of said wet etching vessel by rapidly removing a wafer boat containing said semiconductor wafers from said wet etching vessel in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value.

60. (new) A method for etching a semiconductor wafer, said method comprising:

placing an etching fluid into a wet etching vessel;

placing said semiconductor wafer in said etching fluid;

contacting said semiconductor wafer with said etching fluid for a predetermined time; and

removing a portion of said etching fluid from the upper surface of said wet etching by telescopically collapsing sidewalls of said wet etching vessel in a manner such that the velocity of said portion of said etching fluid rapidly increases at the point of removal from a first value to a second higher value.--

#### REMARKS

Claims 1, 2, 4-27 and 44 remain pending in this application. Claims 48-60 have been newly added.

The amendment filed on October 4, 2000 has been objected to under 35 U.S.C. § 132 as introducing new matter into the application. According to the Office